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				Complete if Known	
				Application Number	09/759,312
				Filing Date	January 12, 2001
				First Named Inventor	Yoshihiro UETA
				Art Unit	2812
				Examiner Name	S. Mulpuri
Sheet	1	of	1	Attorney Docket Number	299002051800

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	1.	Zauner, A.R.A. et al. (1999). "Homoepitaxial Growth on Misoriented GaN Substrates By MOCVD," <i>Proceedings of the Material Research Society Symposium W (GaN and Related Alloys)</i> November 28-December 3, 1999, 595:407 (Abstract W6.3).	

*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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